

Tuning the Electronic and Chemical Properties of Monolayer MoS₂ Adsorbed on Transition Metal Substrates

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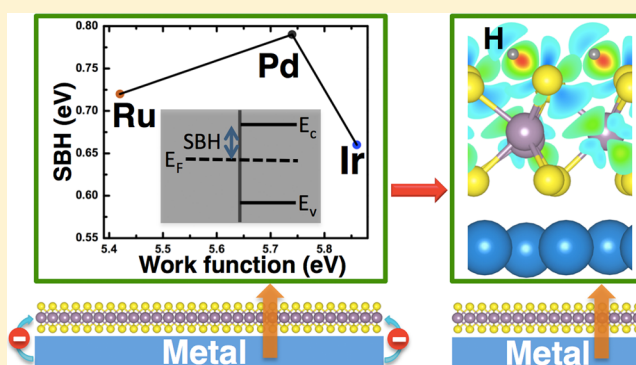
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ABSTRACT: Using first-principles calculations within density functional theory, we investigate the electronic and chemical properties of a single-layer MoS₂ adsorbed on Ir(111), Pd(111), or Ru(0001), three representative transition metal substrates having varying work functions but each with minimal lattice mismatch with the MoS₂ overlayer. We find that, for each of the metal substrates, the contact nature is of Schottky-barrier type, and the dependence of the barrier height on the work function exhibits a partial Fermi-level pinning picture. Using hydrogen adsorption as a testing example, we further demonstrate that the introduction of a metal substrate can substantially alter the chemical reactivity of the adsorbed MoS₂ layer. The enhanced binding of hydrogen, by as much as ~0.4 eV, is attributed in part to a stronger H–S coupling enabled by the transferred charge from the substrate to the MoS₂ overlayer, and in part to a stronger MoS₂–metal interface by the hydrogen adsorption. These findings may prove to be instrumental in future design of MoS₂–based electronics, as well as in exploring novel catalysts for hydrogen production and related chemical processes.

KEYWORDS: Density functional theory, MoS₂–metal contacts, Schottky barrier, hydrogen adsorption, catalyst



As a transition-metal dichalcogenide semiconductor, MoS₂ is a commonly used dry lubricant, whose low-dimensional structures are receiving much research attention because of their distinctive electronic,^{1–3} optical,^{1,4–6} and catalytic properties.^{7–11} Bulk MoS₂ has a layered structure, each layer consisting of a covalently bonded S–Mo–S hexagonal quasi-two-dimensional network,^{12,13} with weak van der Waals (vdW) attraction between the layers. Owing to the relatively weak interlayer interaction, a monolayer of MoS₂ can be mechanically exfoliated from a MoS₂ crystal.¹⁴ Such monolayer systems not only have a direct band gap with highly desirable optical properties¹ but also possess sufficiently high carrier mobility for potential applications in nanoelectronics.¹⁵ In exploring the device potential of monolayer MoS₂, it is vital to understand how such systems interface with metallic contacts, similar to recent developments in other areas of nanomaterials such as semiconductor wires, carbon nanotubes,^{16,17} and graphene.¹⁸ In particular, it was found recently that both the barrier height for electron tunneling and the nature of contact between MoS₂ and an electrode can be drastically altered when using different types of metal contacts.¹⁹ Furthermore, on a different front, monolayer-high MoS₂ islands adsorbed on different metal substrates have been shown to be highly catalytic in hydrogen

evolution reaction (HER),^{8–11} with the reactivity largely attributed to the edge sites of the islands.

In this Letter, we use first-principles calculations within density functional theory (DFT) to investigate the electronic and chemical properties of a single-layer MoS₂ adsorbed on Ir(111), Pd(111), or Ru(0001), three representative transition metal substrates having varying work functions but each with minimal lattice mismatch with the MoS₂ overlayer. We find that for each of the metal substrates, the contact nature is of Schottky-barrier type, and the dependence of the barrier height on the work function establishes a partial Fermi-level (FL) pinning picture.²⁰ Using hydrogen adsorption as a testing example, we further demonstrate that the introduction of a metal substrate can substantially alter the chemical reactivity of the adsorbed MoS₂ layer. Our detailed analysis of the electron density redistribution reveals that the enhanced binding of hydrogen, by as much as ~0.4 eV, is attributed in part to a stronger H–S coupling enabled by the transferred charge from the substrate to the MoS₂ overlayer, and in part to a stronger MoS₂–metal interface by the hydrogen adsorption. These

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Our DFT calculations were carried out using the Vienna *ab initio* simulation package (VASP)²¹ with projector-augmented wave (PAW) pseudopotentials^{22,23} and the Ceperley-Alder local density approximation (LDA)²⁴ as parametrized by Perdew and Zunger²⁵ for the exchange-correlation functional. Unless otherwise specified, the results presented were from LDA calculations. For Pd and Ru as substrates, we have also compared the LDA results with those from DFT-D2,^{26,27} a semiempirical approach that includes vdW interactions, to cross check on the accuracy as well as the overall trends of the LDA results.²⁸ The lattice constants of the metals and the monolayer MoS₂ were obtained via structural optimization. The metal substrates were modeled by slabs of 8 atomic layers, and the MoS₂-metal systems were modeled by placing a single-layer MoS₂ on top of the metal surfaces. A vacuum region more than 15 Å was used to ensure decoupling between neighboring slabs. During structural relaxation, only the bottom layer atoms were fixed in their respective bulk positions, with all the other atoms fully relaxed until the force on any given atom is smaller than 0.01 eV/Å. A $6 \times 6 \times 1$ *k*-point mesh was used for the 2×2 surface unit cell of metals.²⁹ When H adsorption was considered, we also examined the effect of spin polarization in our calculations. The spin-orbit coupling effect has also been checked for the heaviest element, Ir, and the detailed results indicate that it has only negligible influence on the energetics.

We choose Ir(111), Pd(111), and Ru(0001) as substrates mainly because a ($\sqrt{3} \times \sqrt{3}$) R30° unit cell of MoS₂ can nicely match with a 2×2 unit cell of Ir(111), Pd(111), or Ru(0001), as illustrated in Figure 1. The maximum mismatch is $\sim 1.2\%$ for

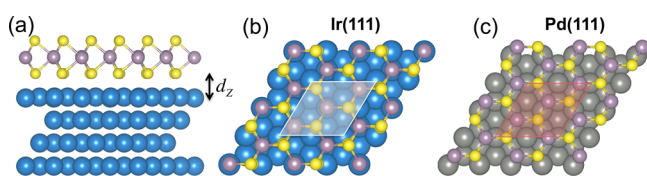


Figure 1. (a) Side and (b) top views of monolayer MoS₂ on the Ir(111) substrate. (c) Top view of MoS₂ on the Pd(111) substrate. In b and c, the white- and red-shaded areas show the unit cells in the calculations, respectively.

Ru(0001), with varying work functions of 5.86 eV, 5.74 eV, and 5.42 eV for Ir(111), Pd(111), and Ru(0001), respectively. In our calculations, the surface lattices of the metal substrates were fixed to their optimized values and the in-plane lattice of MoS₂ was adjusted to match the metal substrates accordingly. The most stable contact geometries were obtained by optimizing the structures from different initial configurations. For all of the systems, the top layer of the metal substrates and the bottom S layer of MoS₂ essentially stay planar after relaxation, with the MoS₂-metal distances listed in Table 1. However, the relative positions between MoS₂ and the substrates along the interface directions are different for different metals. On Ir(111), the three Mo atoms in the supercell sit above the fcc hollow, hcp hollow, and top sites, respectively (Figure 1b); while on Pd(111), the Mo atoms are all above the centers of the triangles formed by the fcc, hcp, and top sites (Figure 1c). The registry of MoS₂ relative to the top layer of Ru(0001) is similar to that of Ir(111) and is therefore omitted in Figure 1. The MoS₂-

Table 1. Structural and Energetic Results for All of the Free-Standing MoS₂ and MoS₂-Metal Systems^a

	E_b (eV)	d_z^0 (Å)	d_z^H (Å)	E_a (eV)	L_{H-S} (Å)	θ (deg)
free-standing MoS ₂				1.07	1.46	40.2
MoS ₂ /Ir(111)	0.62	2.23	2.20	1.44	1.43	37.2
MoS ₂ /Pd(111)	0.74	2.17	2.09	1.39	1.39	89.1
MoS ₂ /Ru(0001)	0.82	2.25	2.20	1.33	1.46	38.2

^a E_b is the binding energy per sulfur atom between MoS₂ and a given substrate; d_z^0 and d_z^H are the distances between MoS₂ and a given metal substrate without and with H adsorption, respectively; E_a is the H binding energy on the planar surface of a free-standing MoS₂ or a MoS₂ overlayer on a given substrate; L_{H-S} is the H-S bond length; θ is the angle between the H-S bond and the planar surface of MoS₂.

metal binding energies per interfacial sulfur atom, calculated as $E_b = (E_{\text{MoS}_2} + E_{\text{metal}} - E_{\text{MoS}_2/\text{metal}})/3$, range from 0.62 to 0.82 eV as listed in Table 1. The inclusion of the vdW interactions increases the binding energy by 0.16 eV for Pd and 0.19 eV for Ru; furthermore, the GGA-vdW results also reduce the interfacial distances between the MoS₂ overlayer and the metal substrates to be close to the LDA results. The even stronger binding energies of the vdW results over LDA, which tends to overestimate the binding,³⁰ should be attributed to the significant attractive contributions of vdW interactions.

To identify the energy level alignment at the interface between MoS₂ and the metal substrates, we have calculated the band structures of MoS₂ and the combined systems. As seen in Figure 2a, the original K point of the 1×1 unit cell where the band edge is located, is folded to the Γ point in the reciprocal space of the $\sqrt{3} \times \sqrt{3}$ superlattice of single-layer MoS₂. The calculated band gap is ~ 1.8 eV, consistent with previous results.^{1,2} In the combined systems, although the energy bands of MoS₂ hybridize with those of the metals to a certain extent, the majority of the MoS₂ bands can still be identified, as marked in red in Figure 2b–d. The FLs of the combined systems always lie in the band gap region of MoS₂, resulting in the formation of a Schottky barrier at the interface for each case. The calculated n-type Schottky barrier heights corresponding to the energy differences between the conduction band minimum and the FLs are 0.66 eV, 0.79 eV, and 0.72 eV for Ir, Pd, and Ru, respectively (Figure 2e). The maximal work function difference is 0.44 eV, while the maximal difference in the Schottky barrier heights is 0.13 eV; we therefore observe a *partial* FL pinning picture²⁰ when the three metals form contacts with monolayer MoS₂. As for likely pinning mechanisms, the picture of metal-induced gap states is typically operative deep in the semiconductor,³¹ suggesting that a single layer of MoS₂ is unlikely to cause strong FL pinning, consistent with the present study. Alternatively, we expect that the sufficiently strong chemical bonding at the interface, the other pinning mechanism,³² may have also contributed to the pinning effects.

There is another angle to view the electronic properties and contact nature at the MoS₂-metal interfaces. If the FL pinning effects were absent, we would have expected Schottky barrier heights of roughly 1.5 eV, 1.4 eV, and 1.1 eV for Ir, Pd, and Ru, respectively, given by the separations between the conduction band minimum and the FL of the monolayer MoS₂ subtracted by the respective work function differences of MoS₂ and Ir, Pd, or Ru. The observed Schottky barrier heights indicate that there exist pronounced FL shifts of the adsorbed MoS₂, given by ~ 1.11 eV, 0.98 eV, and 1.05 eV for Ir, Pd, and Ru, respectively.

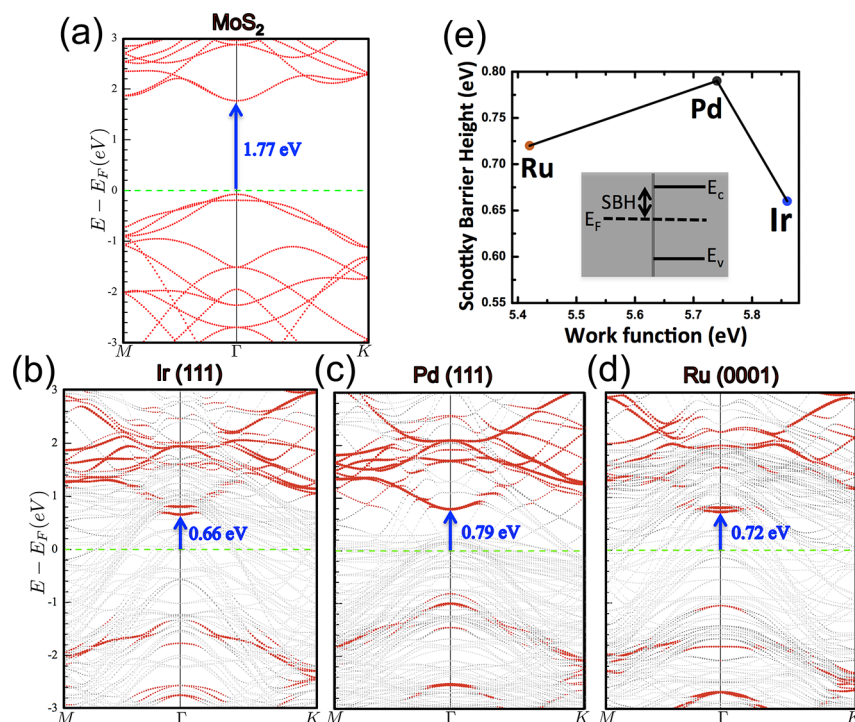


Figure 2. Band structures of (a) a $\sqrt{3} \times \sqrt{3}$ superlattice of monolayer MoS₂, (b) MoS₂-Ir(111), (c) MoS₂-Pd(111), and (d) MoS₂-Ru(0001) interfaces. The Fermi energy E_F is set to zero in all of the four panels and is indicated by the green dashed lines. In b–d, the red lines correspond to the energy bands of the monolayer MoS₂, and the numbers in blue are the Schottky barrier heights, whose dependence on the work function of the metal substrate is plotted in e.

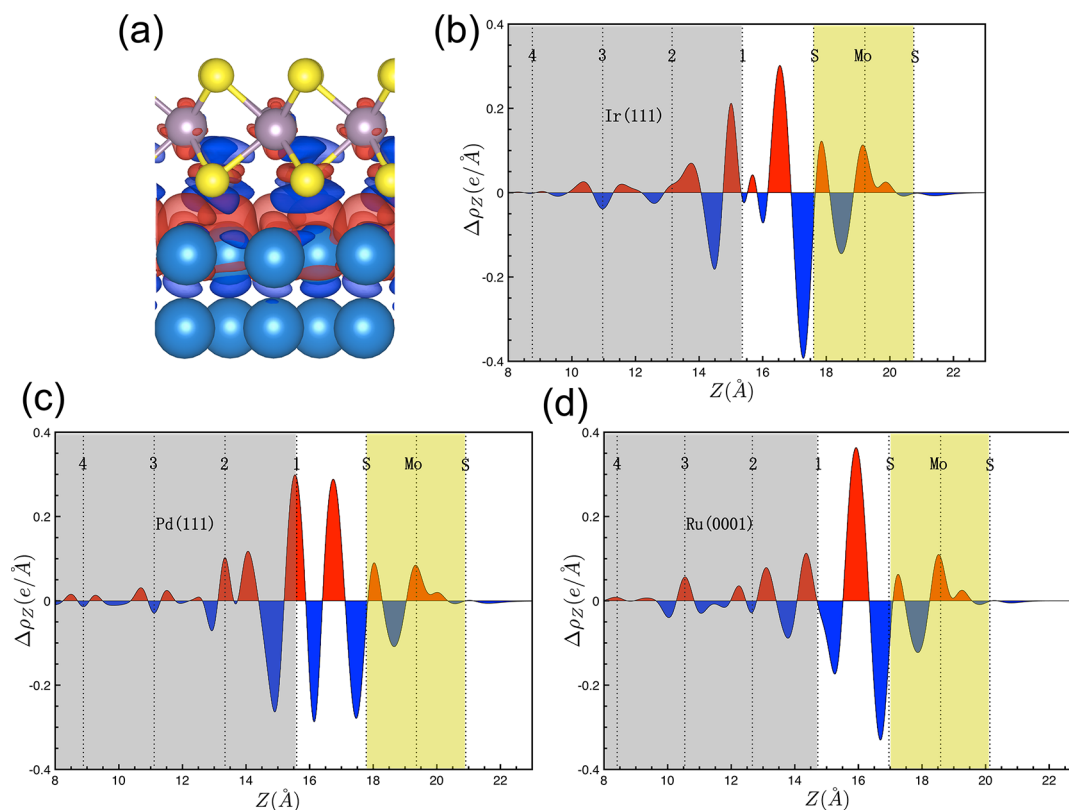


Figure 3. (a) Side view of the charge difference between the combined MoS₂-Ir(111) system and the sum of the isolated MoS₂ and Ir substrate. (b–d) Plots of the plane-averaged electron density difference along the direction perpendicular to the interface ($\Delta\rho_z$) of MoS₂-Ir(111) (b), MoS₂-Pd(111) (c), and MoS₂-Ru(0001) (d). For each case, the reference location $Z = 0$ Å is taken to be the position of the bottom layer of the metal substrate in the slab. The red and blue colors indicate electron accumulation and depletion, respectively.

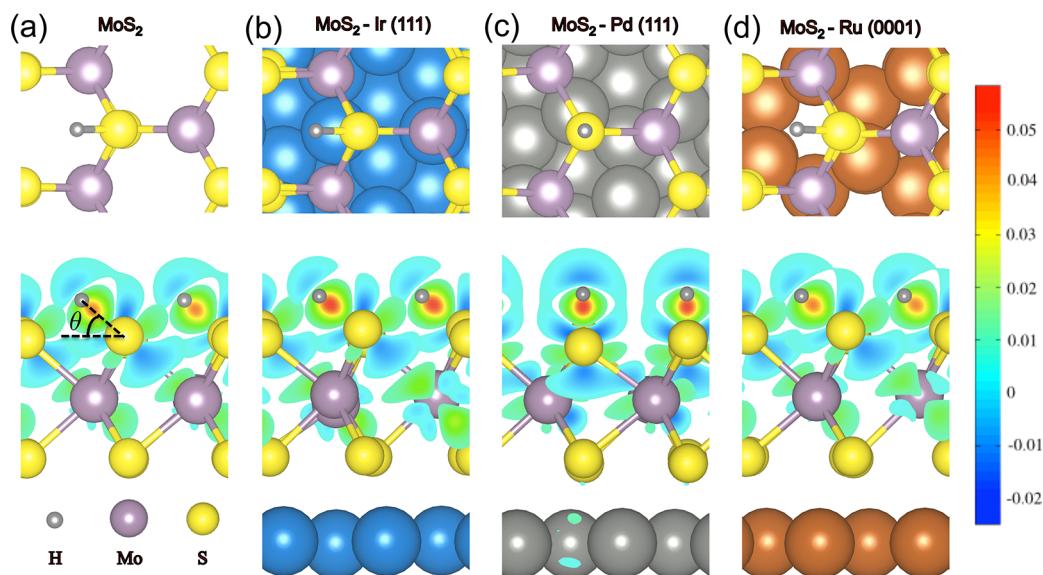


Figure 4. Top views of the bonding geometries (upper row) and cross-sectional views of the charge transfer density (lower row) between a H atom and (a) a free-standing MoS₂, (b) the MoS₂/Ir(111), (c) MoS₂/Pd(111), and (d) MoS₂/Ru(0001) systems. The red and blue colors represent the maximum charge accumulation and maximum charge depletion, respectively.

Similarly, additional FL shifts of up to ~ 0.5 eV were also observed in a previous study of graphene–metal contacts.^{33,34} In both cases, such FL shifts can be induced by the resultant effects of charge transfer at the interfaces and chemical bonding effects; the larger and nonlinear FL shifts are also consistent with the much stronger and varying chemical bondings in the present systems.

To further illustrate the detailed nature of the charge transfer at the MoS₂–metal interfaces, we show in Figure 3a the charge difference between the combined MoS₂–Ir(111) system and the sum of the isolated MoS₂ and Ir substrate. The electronic structures of the isolated MoS₂ and Ir substrate were calculated by freezing the atomic positions of the respective components as obtained in the combined system. The red regions represent charge accumulation, and the blue regions represent depletion of electrons in the combined system relative to the two isolated components. To have a quantitative picture, we plot in Figure 3b–d the plane-averaged electron density difference $\Delta\rho_z$ along the perpendicular direction to the interface. Several charge transfer oscillations are observed at the interfacial region, and some extra charge is found to accumulate around the Mo atoms. Since the position of MoS₂ on Pd(111) is different from that on Ir(111) or Ru(0001), there is a net charge accumulation in the first layer of the Pd substrate closest to MoS₂ (Figure 3c), while the first layer of the Ir and Ru substrates is located at places where the net charge transfer is negligible (Figure 3b and d). Overall, the oscillatory nature of the charge transfer at the interfaces is complex, but our analysis on the FL shifts given above indicates that the adsorbed MoS₂ is net n-type doped by the three investigated metals.

Aside from the transport properties for potential electronic device applications, the significant charge transfer at the MoS₂–metal contacts is also expected to affect the chemical properties of the MoS₂ overlayer. To explore the possibility of tuning the chemical reactivity on the planar surface of MoS₂ through metal substrates, we consider HER as a testing case, which is fundamentally important in a variety of electrochemical processes of technological significance. Currently the most efficient HER catalyst is Pt, which is a precious metal, making it

highly desirable to find alternative catalysts based on materials that are abundant and of low cost. MoS₂ has been demonstrated the ability to function as a HER catalyst, but only the edge sites of the monolayer MoS₂ clusters were identified to be chemically reactive while the planar surface is rather inert.¹⁰ Due to the small lattice mismatches between MoS₂ and the metal substrates considered here, it is expected that large-scale monolayer MoS₂ sheets can be grown on these substrates. Although the planar surface of MoS₂ cannot be as catalytic as the edge sites, considering the large area of the planar surfaces, it is appealing to gain stronger overall reactivity by making the whole planar surfaces sufficiently catalytic. A critical step in HER is that a H⁺ ion gains an electron from the electrode, becoming an atomic H, whose binding energy on the catalytic MoS₂ overlayer placed on the electrode is yet another vital energy scale determining the overall HER efficiency. For this important reason and also for simplicity, we study the influence of different metal substrates on the adsorption energy of atomic H on the MoS₂ overlayer, leaving the electron capture process of H⁺ for a future study.

To find the most stable adsorption site of H on the surface of a given MoS₂ overlayer, we have examined all possible initial positions based on symmetry considerations. Figure 4 depicts the top and side views of the most stable H adsorption geometries on the three metal substrates. The corresponding adsorption energies, calculated as $E_a = E_{\text{hydrogen}} + E_{\text{substrate}} - E_{\text{hydrogen/substrate}}$, are 1.44 eV, 1.39 eV, and 1.33 eV for Ir, Pd, and Ru, respectively (Table 1), all of which are substantially enhanced from the value of 1.07 eV on a free-standing MoS₂. We have verified that the DFT-D2 calculations yield only slightly enhanced binding energies over the LDA results (by less than 0.02 eV). In addition to the binding energy differences, we also observe geometrical differences between the considered systems, as measured by θ , the angle between the H–S bond and the planar surface of MoS₂. As shown in Figure 4 and Table 1, for the systems of MoS₂–Ir(111) and MoS₂–Ru(0001), θ is 37.2° and 38.2°, similar to the angle of 40.2° on the free-standing MoS₂. In contrast, the H adatom prefers an atop position on MoS₂–Pd(111), with $\theta \approx 90^\circ$,

caused by the dramatically different atomic registry between the MoS₂ overlayer and the first layer of the Pd substrate when compared with the other two substrates. Collectively, these results show that both the H binding energy and binding geometry can be tuned with a proper choice of the metal electrode; such tunabilities, in turn, can significantly affect the HER efficiency of the planar MoS₂ overlayer.

To reveal the physical origin of the substrate-enhanced H binding energy, we have calculated the charge transfer between H and the surfaces measured by $\Delta\rho = \rho_{\text{H/MoS}_2/\text{metal}} - \rho_{\text{H}} - \rho_{\text{MoS}_2/\text{metal}}$. The panels shown in the lower row of Figure 4 display the side views of the contour plots of $\Delta\rho$, taken in the plane normal to the interface and across the H–S bond. We see a clear indication that more charge is involved in the covalent H–S bonds on the Ir(111) and Pd(111) substrates, which is also consistent with the shortened bond lengths shown in Table 1. In contrast, little change is observed in the H–S bond on Ru(0001) from the free-standing MoS₂ case, consistent with the observation that the enhancement in the adsorption energy is the smallest among the three metals. Aside from the charge redistribution between the H adatom and the MoS₂ overlayer, we can also investigate the effect of H adsorption on the coupling between the MoS₂ and the substrate. Such effects could be quantified by variations in d_z^{H} , defining the maximum separation of the sulfur atoms in the lower layer of MoS₂ from the topmost layer of the metal substrate. When compared with d_z^0 , the separation without the presence of H, d_z^{H} becomes smaller by 0.03 Å, 0.08 Å, and 0.05 Å for Ir, Pd, and Ru, respectively. These results demonstrate that the enhancements in the adsorption energy arise from two aspects: one is the stronger H–S covalent bonding enabled by the transferred charge from the metal substrates to MoS₂; the other is associated with the stronger MoS₂–metal interfaces caused by the H adatom serving as a “nail” to pin the MoS₂ and substrate together.

Before closing, we note that the significant net charge transfer from the metal substrates to the MoS₂ overlayer will likely have an even stronger effect on the electron capture process of H⁺ ion. This intriguing possibility will be examined in a future study of a more complete HER cycle.

In summary, we have investigated the electronic and chemical properties of a single-layer MoS₂ adsorbed on Ir(111), Pd(111), or Ru(0001). We found that for each of the metal substrates, the contact nature is of Schottky-barrier type, and the dependence of the Schottky barrier height on the work function establishes a partial Fermi-level pinning picture for these systems. We have further demonstrated that the introduction of a metal substrate can substantially alter the H binding energy on the MoS₂ overlayer. A detailed analysis of the electron density redistribution revealed that the enhanced binding of hydrogen is the result of a stronger H–S coupling enabled by the transferred charge from the substrate to the MoS₂ overlayer, and a stronger MoS₂–metal interaction caused by the hydrogen adsorption. These findings may prove to be instrumental in future design of MoS₂–based electronics, as well as in searching for novel catalysts for hydrogen production and related chemical processes.

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Notes

The authors declare no competing financial interest.

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